Lattice Semiconductor Corporation - LCMXO2-2000HC-5TG144C Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	111
Number of Gates	-
Voltage - Supply	2.375V ~ 3.465V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-2000hc-5tg144c

Programmable I/O Cells (PIC)

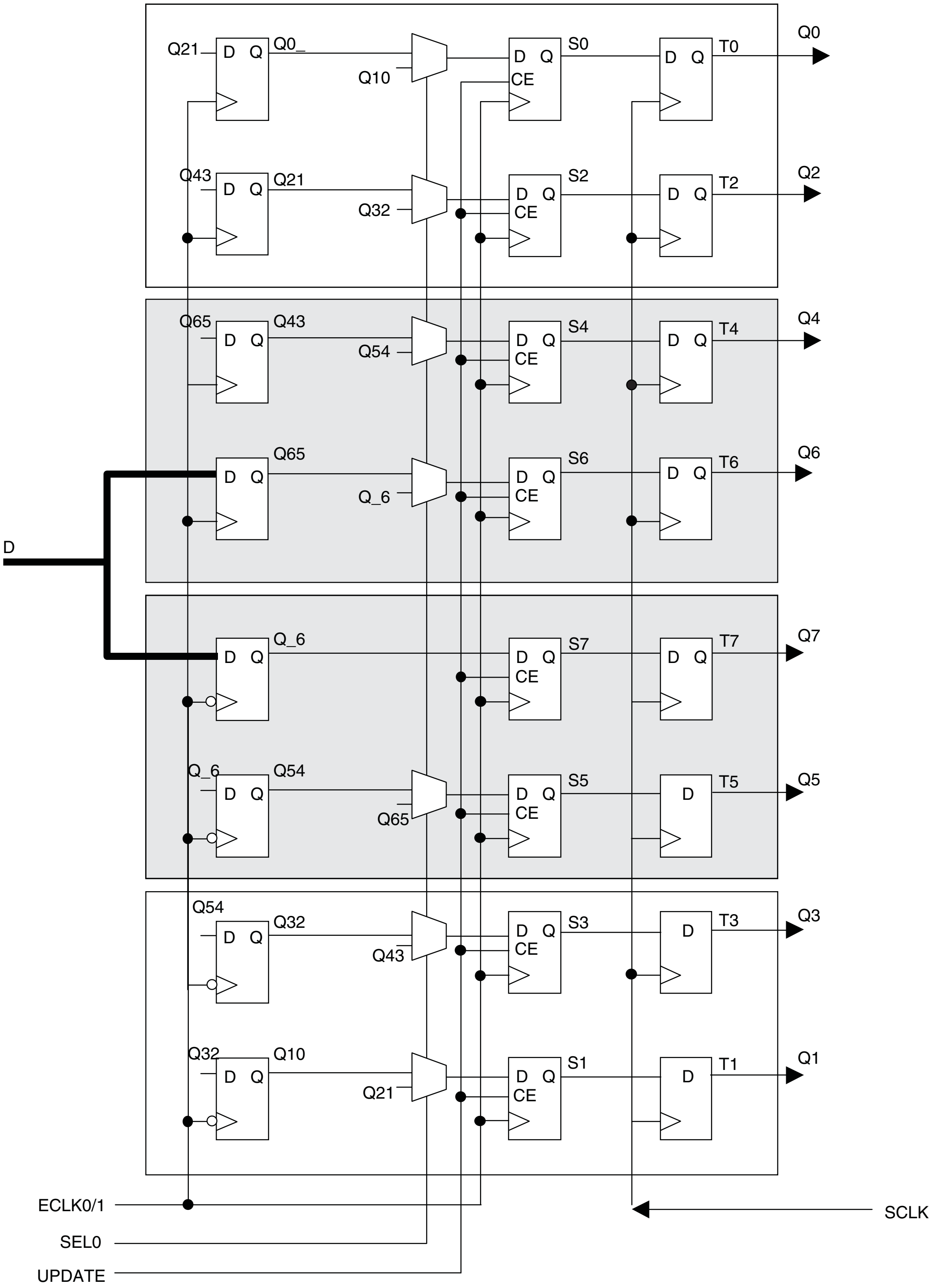
The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-16 shows a block diagram of the input gearbox.

Figure 2-16. Input Gearbox



DDR Memory Support

Certain PICs on the right edge of MachXO2-640U, MachXO2-1200/U and larger devices, have additional circuitry to allow the implementation of DDR memory interfaces. There are two groups of 14 or 12 PIOs each on the right edge with additional circuitry to implement DDR memory interfaces. This capability allows the implementation of up to 16-bit wide memory interfaces. One PIO from each group contains a control element, the DQS Read/Write Block, to facilitate the generation of clock and control signals (DQSR90, DQSW90, DDRCLKPOL and DATAVALID). These clock and control signals are distributed to the other PIO in the group through dedicated low skew routing.

DQS Read Write Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Read Write block provides the required clock alignment for DDR memory interfaces. DQSR90 and DQSW90 signals are generated by the DQS Read Write block from the DQS input.

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the read cycle) is unknown. The MachXO2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This circuit changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each read cycle for the correct clock polarity. Prior to the read operation in DDR memories, DQS is in tri-state (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit in the DQS Read Write block detects the first DQS rising edge after the preamble state and generates the DDRCLKPOL signal. This signal is used to control the polarity of the clock to the synchronizing registers.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of calibration signals (6-bit bus) from a DLL on the right edge of the device. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, SSTL, HSTL, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO2 devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) and referenced input buffers (SSTL and HSTL) are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO}. In addition, each bank has a voltage reference, V_{REF}, which allows the use of referenced input buffers independent of the bank V_{CCIO}.

MachXO2-256 and MachXO2-640 devices contain single-ended ratioed input buffers and single-ended output buffers with complementary outputs on all the I/O banks. Note that the single-ended input buffers on these devices do not contain PCI clamps. In addition to the single-ended I/O buffers these two devices also have differential and referenced input buffers on all I/Os. The I/Os are arranged in pairs, the two pads in the pair are described as “T” and “C”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

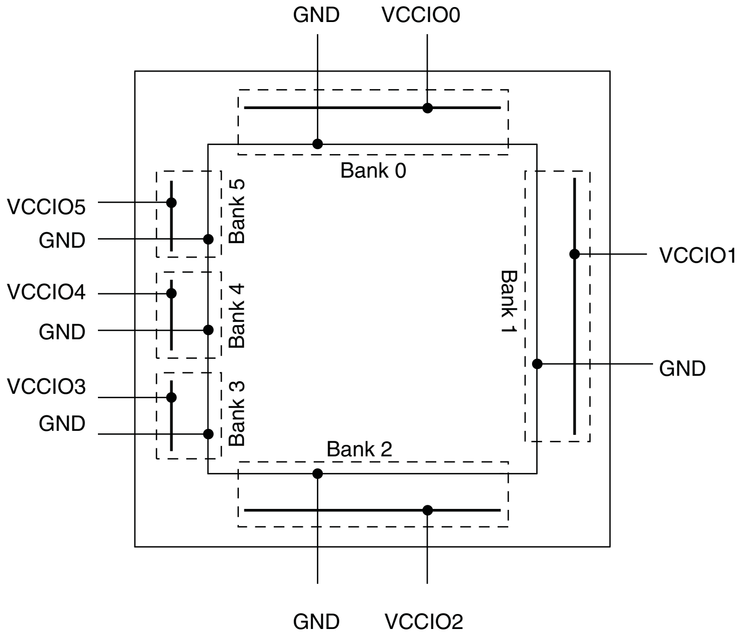
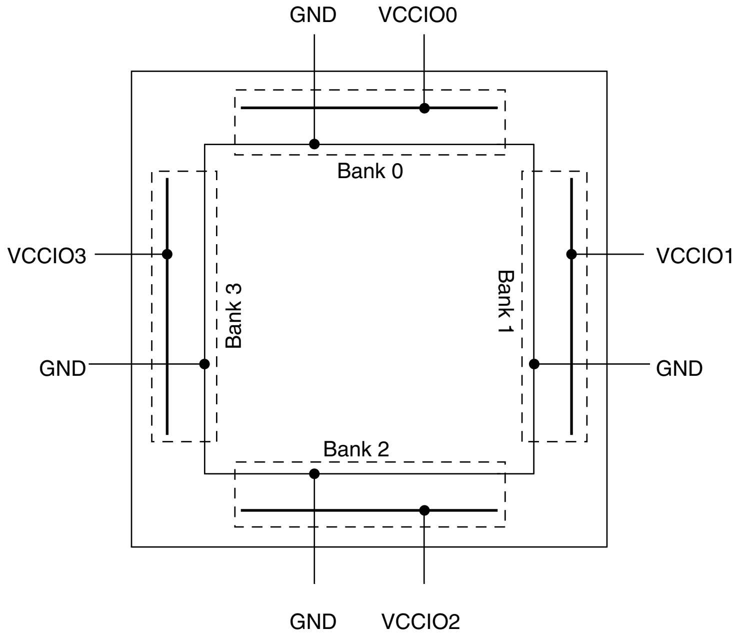


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



Static Supply Current – ZE Devices[1, 2, 3, 6]

Symbol	Parameter	Device	Typ.[4]	Units
I_{CC}	Core Power Supply	LCMXO2-256ZE	18	µA
		LCMXO2-640ZE	28	µA
		LCMXO2-1200ZE	56	µA
		LCMXO2-2000ZE	80	µA
		LCMXO2-4000ZE	124	µA
		LCMXO2-7000ZE	189	µA
I_{CCIO}	Bank Power Supply[5] V_{CCIO} = 2.5 V	All devices	1	µA

1. For further information on supply current, please refer to TN1198, Power Estimation and Management for MachXO2 Devices.
2. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip oscillator is off, on-chip PLL is off. To estimate the impact of turning each of these items on, please refer to the following table or for more detail with your specific design use the Power Calculator tool.
3. Frequency = 0 MHz.
4. T_J = 25 °C, power supplies at nominal voltage.
5. Does not include pull-up/pull-down.
6. To determine the MachXO2 peak start-up current data, use the Power Calculator tool.

Static Power Consumption Contribution of Different Components – ZE Devices

The table below can be used for approximating static power consumption. For a more accurate power analysis for your design please use the Power Calculator tool.

Symbol	Parameter	Typ.	Units
I_{DCBG}	Bandgap DC power contribution	101	µA
I_{DCPOR}	POR DC power contribution	38	µA
$I_{DCIOBANKCONTROLLER}$	DC power contribution per I/O bank controller	143	µA

sysIO Single-Ended DC Electrical Characteristics[1, 2]

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max.[4] (mA)	I_{OH} Max.[4] (mA)
	Min. (V)[3]	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
							16	–16
							24	–24
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 2.5	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
							16	–16
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.8	–0.3	0.35V_{CCIO}	0.65V_{CCIO}	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
							12	–12
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.5	–0.3	0.35V_{CCIO}	0.65V_{CCIO}	3.6	0.4	V_{CCIO} – 0.4	4	–4
							8	–8
					0.2	V_{CCIO} – 0.2	0.1	–0.1
LVCMOS 1.2	–0.3	0.35V_{CCIO}	0.65V_{CCIO}	3.6	0.4	V_{CCIO} – 0.4	4	–2
							8	–6
					0.2	V_{CCIO} – 0.2	0.1	–0.1
PCI	–0.3	0.3V_{CCIO}	0.5V_{CCIO}	3.6	0.1V_{CCIO}	0.9V_{CCIO}	1.5	–0.5
SSTL25 Class I	–0.3	V_{REF} – 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	8	8
SSTL25 Class II	–0.3	V_{REF} – 0.18	V_{REF} + 0.18	3.6	NA	NA	NA	NA
SSTL18 Class I	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.6	0.40	V_{CCIO} - 0.40	8	8
SSTL18 Class II	–0.3	V_{REF} – 0.125	V_{REF} + 0.125	3.6	NA	NA	NA	NA
HSTL18 Class I	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	V_{CCIO} - 0.40	8	8
HSTL18 Class II	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS25R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max.[4] (mA)	I_{OH} Max.[4] (mA)
	Min. (V)[3]	Max. (V)	Min. (V)	Max. (V)				
LVCMOS10R25	–0.3	V_{REF} – 0.1	V_{REF} + 0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO2 devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO2 devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO2 devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1202, MachXO2 sysIO Usage Guide.
3. The dual function I^2C pins SCL and SDA are limited to a V_{IL} min of –0.25 V or to –0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive VCCIO or GND pad connections, or between the last VCCIO or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. “n” is the number of I/O pads between the two consecutive bank VCCIO or GND connections or between the last VCCIO and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

Input Standard	V_{CCIO} (V)	V_{IL} Max. (V)
LVCMOS 33	1.5	0.685
LVCMOS 25	1.5	0.687
LVCMOS 18	1.5	0.655

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of MachXO2-640U, MachXO2-1200/U and higher density devices in the MachXO2 PLD family.

LVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V_{INP}, V_{INM}	Input Voltage	V_{CCIO} = 3.3 V	0	—	2.605	V
		V_{CCIO} = 2.5 V	0	—	2.05	V
V_{THD}	Differential Input Threshold		±100	—		mV
V_{CM}	Input Common Mode Voltage	V_{CCIO} = 3.3 V	0.05	—	2.6	V
		V_{CCIO} = 2.5 V	0.05	—	2.0	V
I_{IN}	Input current	Power on	—	—	±10	µA
V_{OH}	Output high voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	—	1.375	—	V
V_{OL}	Output low voltage for V_{OP} or V_{OM}	R_T = 100 Ohm	0.90	1.025	—	V
V_{OD}	Output voltage differential	(V_{OP} - V_{OM}), R_T = 100 Ohm	250	350	450	mV
ΔV_{OD}	Change in V_{OD} between high and low		—	—	50	mV
V_{OS}	Output voltage offset	(V_{OP} + V_{OM})/2, R_T = 100 Ohm	1.125	1.20	1.395	V
ΔV_{OS}	Change in V_{OS} between H and L		—	—	50	mV
I_{OSD}	Output short circuit current	V_{OD} = 0 V driver outputs shorted	—	—	24	mA

Maximum sysIO Buffer Performance

I/O Standard	Max. Speed	Units
LVDS25	400	MHz
LVDS25E	150	MHz
RSDS25	150	MHz
RSDS25E	150	MHz
BLVDS25	150	MHz
BLVDS25E	150	MHz
MLVDS25	150	MHz
MLVDS25E	150	MHz
LVPECL33	150	MHz
LVPECL33E	150	MHz
SSTL25_I	150	MHz
SSTL25_II	150	MHz
SSTL25D_I	150	MHz
SSTL25D_II	150	MHz
SSTL18_I	150	MHz
SSTL18_II	150	MHz
SSTL18D_I	150	MHz
SSTL18D_II	150	MHz
HSTL18_I	150	MHz
HSTL18_II	150	MHz
HSTL18D_I	150	MHz
HSTL18D_II	150	MHz
PCI33	134	MHz
LVTTL33	150	MHz
LVTTL33D	150	MHz
LVCMOS33	150	MHz
LVCMOS33D	150	MHz
LVCMOS25	150	MHz
LVCMOS25D	150	MHz
LVCMOS25R33	150	MHz
LVCMOS18	150	MHz
LVCMOS18D	150	MHz
LVCMOS18R33	150	MHz
LVCMOS18R25	150	MHz
LVCMOS15	150	MHz
LVCMOS15D	150	MHz
LVCMOS15R33	150	MHz
LVCMOS15R25	150	MHz
LVCMOS12	91	MHz
LVCMOS12D	91	MHz

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.369	—	0.395	—	0.421	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.529	—	0.530	—	0.527	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	280	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	140	—	125	—	104	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	280	0	250	0	208	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.350	—	0.387	—	0.414	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.545	—	0.538	—	0.532	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.360	—	0.378	—	0.406	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.555	—	0.549	—	0.542	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\text{ ns})/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
8. This number for general purpose usage. Duty cycle tolerance is +/– 10%.
9. Duty cycle is +/–5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32 QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.349	—	0.381	—	0.396	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.630	—	0.613	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	120	—	110	—	96	Mbps
f_{SCLK}	SCLK Frequency		—	60	—	55	—	48	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	120	0	110	0	96	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.347	—	0.374	—	0.393	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.665	—	0.637	—	0.616	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.372	—	0.394	—	0.410	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.690	—	0.658	—	0.618	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	140	—	116	—	98	Mbps
f_{SCLK}	SCLK Frequency		—	70	—	58	—	49	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	140	N/A	116	N/A	98	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0 pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\ ns)/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 167 ps (–3), 182 ps (–2), 195 ps (–1).
8. This number for general purpose usage. Duty cycle tolerance is +/–10%.
9. Duty cycle is +/– 5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32-Pin QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Flash Download Time[1, 2]

Symbol	Parameter	Device	Typ.	Units
$t_{REFRESH}$	POR to Device I/O Active	LCMXO2-256	0.6	ms
		LCMXO2-640	1.0	ms
		LCMXO2-640U	1.9	ms
		LCMXO2-1200	1.9	ms
		LCMXO2-1200U	1.4	ms
		LCMXO2-2000	1.4	ms
		LCMXO2-2000U	2.4	ms
		LCMXO2-4000	2.4	ms
		LCMXO2-7000	3.8	ms

1. Assumes sysMEM EBR initialized to an all zero pattern if they are used.
2. The Flash download time is measured starting from the maximum voltage of POR trip point.

JTAG Port Timing Specifications

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	20	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Signal Descriptions (Cont.)

Signal Name	I/O	Descriptions
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, or when reserved as INITn in user mode, this pin has an active pull-up.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the start-up sequence is in progress. During configuration, or when reserved as DONE in user mode, this pin has an active pull-up.
MCLK/CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA in SPI and SPIm configuration modes.
SN	I	Slave SPI active low chip select input.
CSSPIN	I/O	Master SPI active low chip select output.
SI/SPISI	I/O	Slave SPI serial data input and master SPI serial data output.
SO/SPISO	I/O	Slave SPI serial data output and master SPI serial data input.
SCL	I/O	Slave I^{2}C clock input and master I^{2}C clock output.
SDA	I/O	Slave I^{2}C data input and master I^{2}C data output.

	MachXO2-4000							
	84 QFN	132 csBGA	144 TQFP	184 csBGA	256 caBGA	256 ftBGA	332 caBGA	484 fpBGA
General Purpose I/O per Bank								
Bank 0	27	25	27	37	50	50	68	70
Bank 1	10	26	29	37	52	52	68	68
Bank 2	22	28	29	39	52	52	70	72
Bank 3	0	7	9	10	16	16	24	24
Bank 4	9	8	10	12	16	16	16	16
Bank 5	0	10	10	15	20	20	28	28
Total General Purpose Single Ended I/O	68	104	114	150	206	206	274	278
Differential I/O per Bank								
Bank 0	13	13	14	18	25	25	34	35
Bank 1	4	13	14	18	26	26	34	34
Bank 2	11	14	14	19	26	26	35	36
Bank 3	0	3	4	4	8	8	12	12
Bank 4	4	4	5	6	8	8	8	8
Bank 5	0	5	5	7	10	10	14	14
Total General Purpose Differential I/O	32	52	56	72	103	103	137	139
Dual Function I/O	28	37	37	37	37	37	37	37
High-speed Differential I/O								
Bank 0	8	8	9	8	18	18	18	18
Gearboxes								
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	8	8	9	9	18	18	18	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	11	14	14	12	18	18	18	18
DQS Groups								
Bank 1	1	2	2	2	2	2	2	2
VCCIO Pins								
Bank 0	3	3	3	3	4	4	4	10
Bank 1	1	3	3	3	4	4	4	10
Bank 2	2	3	3	3	4	4	4	10
Bank 3	1	1	1	1	1	1	2	3
Bank 4	1	1	1	1	2	2	1	4
Bank 5	1	1	1	1	1	1	2	3
VCC	4	4	4	4	8	8	8	12
GND	4	10	12	16	24	24	27	48
NC	1	1	1	1	1	1	5	105
Reserved for configuration	1	1	1	1	1	1	1	1
Total Count of Bonded Pins	84	132	144	184	256	256	332	484

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4SG32C	1280	2.5 V / 3.3 V	–4	Halogen-Free QFN	32	COM
LCMXO2-1200HC-5SG32C	1280	2.5 V / 3.3 V	–5	Halogen-Free QFN	32	COM
LCMXO2-1200HC-6SG32C	1280	2.5 V / 3.3 V	–6	Halogen-Free QFN	32	COM
LCMXO2-1200HC-4TG100C	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-5TG100C	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-6TG100C	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-1200HC-4MG132C	1280	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-5MG132C	1280	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-6MG132C	1280	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-1200HC-4TG144C	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-1200HC-5TG144C	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-1200HC-6TG144C	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200UHC-4FTG256C	1280	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-1200UHC-5FTG256C	1280	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-1200UHC-6FTG256C	1280	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HC-4TG100C	2112	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-2000HC-5TG100C	2112	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-2000HC-6TG100C	2112	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-2000HC-4MG132C	2112	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-2000HC-5MG132C	2112	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-2000HC-6MG132C	2112	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-2000HC-4TG144C	2112	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-2000HC-5TG144C	2112	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-2000HC-6TG144C	2112	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-2000HC-4BG256C	2112	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-2000HC-5BG256C	2112	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-2000HC-6BG256C	2112	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-2000HC-4FTG256C	2112	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-2000HC-5FTG256C	2112	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-2000HC-6FTG256C	2112	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM

High-Performance Commercial Grade Devices without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100C	2112	1.2 V	–4	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-5TG100C	2112	1.2 V	–5	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-6TG100C	2112	1.2 V	–6	Halogen-Free TQFP	100	COM
LCMXO2-2000HE-4TG144C	2112	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-5TG144C	2112	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-6TG144C	2112	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-2000HE-4MG132C	2112	1.2 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-5MG132C	2112	1.2 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-6MG132C	2112	1.2 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-2000HE-4BG256C	2112	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-5BG256C	2112	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-6BG256C	2112	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-2000HE-4FTG256C	2112	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-2000HE-5FTG256C	2112	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-2000HE-6FTG256C	2112	1.2 V	–6	Halogen-Free ftBGA	256	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484C	2112	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHE-5FG484C	2112	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHE-6FG484C	2112	1.2 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-4TG144C	4320	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-5TG144C	4320	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-6TG144C	4320	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HE-4MG132C	4320	1.2 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-5MG132C	4320	1.2 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-6MG132C	4320	1.2 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HE-4BG256C	4320	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-4MG184C	4320	1.2 V	–4	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-5MG184C	4320	1.2 V	–5	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-6MG184C	4320	1.2 V	–6	Halogen-Free csBGA	184	COM
LCMXO2-4000HE-5BG256C	4320	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-6BG256C	4320	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HE-4FTG256C	4320	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-5FTG256C	4320	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-6FTG256C	4320	1.2 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HE-4BG332C	4320	1.2 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HE-5BG332C	4320	1.2 V	–5	Halogen-Free caBGA	332	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-6BG332C	4320	1.2 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-4000HE-4FG484C	4320	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HE-5FG484C	4320	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HE-6FG484C	4320	1.2 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HE-4TG144C	6864	1.2 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-5TG144C	6864	1.2 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-6TG144C	6864	1.2 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-7000HE-4BG256C	6864	1.2 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-5BG256C	6864	1.2 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-6BG256C	6864	1.2 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-7000HE-4FTG256C	6864	1.2 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-5FTG256C	6864	1.2 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-6FTG256C	6864	1.2 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-7000HE-4BG332C	6864	1.2 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-5BG332C	6864	1.2 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-6BG332C	6864	1.2 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-7000HE-4FG484C	6864	1.2 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-7000HE-5FG484C	6864	1.2 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-7000HE-6FG484C	6864	1.2 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200HC-4TG100IR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-5TG100IR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-6TG100IR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-1200HC-4MG132IR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-5MG132IR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-6MG132IR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-1200HC-4TG144IR1[1]	1280	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-5TG144IR1[1]	1280	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-1200HC-6TG144IR1[1]	1280	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	IND

1. Specifications for the “LCMXO2-1200HC-speed package IR1” are the same as the “LCMXO2-1200ZE-speed package I” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

MachXO2 Family Data Sheet Supplemental Information

April 2012 **Data Sheet DS1035**

For Further Information

A variety of technical notes for the MachXO2 family are available on the Lattice web site.

- TN1198, Power Estimation and Management for MachXO2 Devices
- TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide
- TN1201, Memory Usage Guide for MachXO2 Devices
- TN1202, MachXO2 sysIO Usage Guide
- TN1203, Implementing High-Speed Interfaces with MachXO2 Devices
- TN1204, MachXO2 Programming and Configuration Usage Guide
- TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices
- TN1206, MachXO2 SRAM CRC Error Detection Usage Guide
- TN1207, Using TraceID in MachXO2 Devices
- TN1074, PCB Layout Recommendations for BGA Packages
- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology
- AN8086, Designing for Migration from MachXO2-1200-R1 to Standard (non-R1) Devices
- AN8066, Boundary Scan Testability with Lattice sysIO Capability

- MachXO2 Device Pinout Files
- Thermal Management document
- Lattice design tools

For further information on interface standards, refer to the following web sites:

- JEDEC Standards (LVTTL, LVCMOS, LVDS, DDR, DDR2, LPDDR): www.jedec.org
- PCI: www.pcisig.com

Date	Version	Section	Change Summary
May 2016	3.2	All	Moved designation for 84 QFN package information from 'Advanced' to 'Final'.
		Introduction	Updated the Features section. Revised Table 1-1, MachXO2 Family Selection Guide. — Added ‘Advanced’ 48 QFN package. — Revised footnote 6. — Added footnote 9.
		DC and Switching Characteristics	Updated the MachXO2 External Switching Characteristics – HC/HE Devices section. Added footnote 12.
			Updated the MachXO2 External Switching Characteristics – ZE Devices section. Added footnote 12.
		Pinout Information	Updated the Signal Descriptions section. Added information on GND signal.
			Updated the Pinout Information Summary section. — Added ‘Advanced’ MachXO2-256 48 QFN values. — Added ‘Advanced’ MachXO2-640 48 QFN values. — Added footnote to GND. — Added footnotes 2 and 3.
		Ordering Information	Updated the MachXO2 Part Number Description section. Added ‘Advanced’ SG48 package and revised footnote.
			Updated the Ordering Information section. — Added part numbers for ‘Advanced’ QFN 48 package.
March 2016	3.1	Introduction	Updated the Features section. Revised Table 1-1, MachXO2 Family Selection Guide. — Added 32 QFN value for XO2-1200. — Added 84 QFN (7 mm x 7 mm, 0.5 mm) package. — Modified package name to 100-pin TQFP. — Modified package name to 144-pin TQFP. — Added footnote.
		Architecture	Updated the Typical I/O Behavior During Power-up section. Removed reference to TN1202.
		DC and Switching Characteristics	Updated the sysCONFIG Port Timing Specifications section. Revised $t_{DPPDONE}$ and $t_{DPPINIT}$ Max. values per PCN 03A-16, released March 2016.
		Pinout Information	Updated the Pinout Information Summary section. — Added MachXO2-1200 32 QFN values. — Added ‘Advanced’ MachXO2-4000 84 QFN values.
		Ordering Information	Updated the MachXO2 Part Number Description section. Added ‘Advanced’ QN84 package and footnote.
			Updated the Ordering Information section. — Added part numbers for 1280 LUTs QFN 32 package. — Added part numbers for 4320 LUTs QFN 84 package.
March 2015	3.0	Introduction	Updated the Features section. Revised Table 1-1, MachXO2 Family Selection Guide. — Changed 64-ball ucBGA dimension.
		Architecture	Updated the Device Configuration section. Added JTAGENB to TAP dual purpose pins.

Date	Version	Section	Change Summary
May 2014	2.5	Architecture	Updated TransFR (Transparent Field Reconfiguration) section. Updated TransFR description for PLL use during background Flash programming.
February 2014	02.4	Introduction	Included the 49 WLCSP package in the MachXO2 Family Selection Guide table.
		Architecture	Added information to Standby Mode and Power Saving Options section.
		Pinout Information	Added the XO2-2000 49 WLCSP in the Pinout Information Summary table.
		Ordering Information	Added UW49 package in MachXO2 Part Number Description.
			Added and LCMXO2-2000ZE-1UWG49CTR in Ultra Low Power Commercial Grade Devices, Halogen Free (RoHS) Packaging section.
			Added and LCMXO2-2000ZE-1UWG49ITR in Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging section.
December 2013	02.3	Architecture	Updated information on CLKOS output divider in sysCLOCK Phase Locked Loops (PLLs) section.
		DC and Switching Characteristics	Updated Static Supply Current – ZE Devices table.
			Updated footnote 4 in sysIO Single-Ended DC Electrical Characteristics table; Updated V_{IL} Max. (V) data for LVCMOS 25 and LVCMOS 28.
			Updated V_{OS} test condition in sysIO Differential Electrical Characteristics - LVDS table.
September 2013	02.2	Architecture	Removed I^2C Clock-Stretching feature per PCN #10A-13.
			Removed information on PDPR memory in RAM Mode section.
			Updated Supported Input Standards table.
		DC and Switching Characteristics	Updated Power-On-Reset Voltage Levels table.
June 2013	02.1	Architecture	Architecture Overview – Added information on the state of the register on power up and after configuration.
			sysCLOCK Phase Locked Loops (PLLs) section – Added missing cross reference to sysCLOCK PLL Timing table.
		DC and Switching Characteristics	Added slew rate information to footnote 2 of the MachXO2 External Switching Characteristics – HC/HE Devices and the MachXO2 External Switching Characteristics – ZE Devices tables.
			Power-On-Reset Voltage Levels table – Added symbols.